



JA01000175P54FS; 100 MHz – 175 MHz 250W Amplifier

- Solid-state Class AB design
- Ruggedized MOS Transistors
- MOS Transistors
- High reliability and ruggedness
- Ultra Small Dimensions & Ultra Light Weight
- Forward/Reflected Power Monitorings
- Temperature and Current Monitorings
- Enable Control



ELECTRICAL & ENVIRONMENTAL SPECIFICATIONS

Frequency:	100-175 MHz
Output Power:	250 W CW
Nominal Gain:	54 dB
Gain Flatness:	± 2 dB
Input VSWR:	2:1 max.
Load VSWR for Survival:	∞:1 for 1 min.
DC Supply Voltage:	28 V
DC Current:	20 A Avg
Operating Case Temp.:	-40 °C to 85 °C
Storage Temperature:	-40 °C to 85 °C
Shock:	MIL-STD-810F/G
Vibration:	MIL-STD-810F/G

INTERFACES

RF Input:	SMA Female
RF Output:	N Female
7W2 COMBO:	A1) GND
	A2) 28 V
	1) N.C.
	2) Temperature*
	3) Enable (Active Low)
	4) Forward Power
	5) Reflected Power

*Temp(°C) = (Voltage(mV) - 1000) / 20

MECHANICAL SPECIFICATIONS

Size (mm) :	190 x 170 x 34
(inch) :	7.48 x 6.69 x 1.34
Weight :	1560 gr.
Plating :	Yellow Chromate

